

Please grant any extensions of time under 37 C.F.R. § 1.136 required in entering this response. If there are any fees due under 37 C.F.R. § 1.16 or 1.17, which are not enclosed, including any fees required for an extension of time under 37 C.F.R. § 1.136, please charge such fees to our deposit account 06-0916.

Respectfully submitted,

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Dated: June 7, 2002

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**APPENDIX TO AMENDMENT OF June 4, 2002**

**Version of Claim with Markings to Show Changes Made**

**AMENDMENTS TO THE CLAIM:**

Please amend claim 1 as follows:

1. (Twice Amended) A semiconductor device comprising:

a semiconductor substrate having a main plane in which a channel of a transistor is formed, the semiconductor substrate comprising a first region and a second region defined in a section taken along a direction of a channel length, the second region having a surface located lower than that of the first region, and the second region being connected to the first region;

a gate insulating film formed on the first region and containing silicon, nitrogen and oxygen;

a gate electrode formed on the gate insulating film, a lower edge of the gate electrode being in a round shape and containing silicon; and

a post oxide film formed on the second region, containing silicon and oxygen and arranged to be in contact with the gate insulating film and the lower edge of the gate electrode [and the gate insulating film].

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